

## PALM INTRANET

Day : Tuesday  
Date: 9/17/2002  
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## Inventor Name Search Result

Your Search was:

Last Name = WANG

First Name = ZHONGZE

Application#	Patent#	Status	Date Filed	Title	Inventor Name
<u>09146296</u>	Not Issued	071	09/03/1998	METHODS OF PASSIVATING AN OXIDE SURFACE SUBJECTED TO A CONDUCTIVE MATERIAL ANNEAL	WANG , ZHONGZE
<u>09165754</u>	<u>6277674</u>	150	10/02/1998	SEMICONDUCTOR FUSES, METHODS OF USING THE SAME, METHODS OF MAKING THE SAME, AND SEMICONDUCTOR DEVICES CONTAINING THE SAME	WANG , ZHONGZE
<u>09386076</u>	<u>6093661</u>	150	08/30/1999	INTEGRATED CIRCUITRY AND SEMICONDUCTOR PROCESSING METHOD OF FORMING FIELD EFFECT TRANSISTORS	WANG , ZHONGZE
<u>09389295</u>	<u>6162693</u>	150	09/02/1999	CHANNEL IMPLANT THROUGH GATE POLYSILICON	WANG , ZHONGZE
<u>09444024</u>	<u>6417546</u>	150	11/19/1999	MOSFET WITH NITROGEN ATOMS IN THE GATE OXIDE	WANG , ZHONGZE
<u>09441912</u>	Not Issued	041	11/17/1999	TWIN WELL METHODS OF FORMING CMOS INTEGRATED CIRCUITRY	WANG , ZHONGZE
<u>10073723</u>	Not Issued	030	02/11/2002	FET HAVING EPITAXIAL SILICON GROWTH	WANG , ZHONGZE
<u>09616959</u>	Not Issued	071	07/13/2000	"SEMICONDUCTOR PROCESSING METHOD OF FORMING FIELD EFFECT TRANSISTORS"	WANG , ZHONGZE
<u>09631329</u>	Not Issued	093	08/03/2000	METHOD OF PASSIVATING AN OXIDE SURFACE SUBJECTED TO A CONDUCTIVE MATERIAL	WANG , ZHONGZE

				ANNEAL	
<u>09901761</u>	Not Issued	093	07/09/2001	SEMICONDUCTOR FUSES, METHODS OF USING THE SAME, METHODS OF MAKING THE SAME, AND SEMICONDUCTOR DEVICES CONTAINING THE SAME	WANG, ZHONGZE
<u>09881407</u>	Not Issued	030	06/13/2001	METHODS OF FORMING TRANSISTOR DEVICES	WANG, ZHONGZE
<u>09945380</u>	Not Issued	041	08/31/2001	CROSS-DIFFUSION RESISTANT DUAL-POLYCID SEMICONDUCTOR STRUCTURE AND METHOD	WANG, ZHONGZE
<u>09945337</u>	Not Issued	041	08/31/2001	SIDEWALL STRAP FOR COMPLEMENTARY SEMICONDUCTOR STRUCTURES AND METHOD OF MAKING SAME	WANG, ZHONGZE
<u>09945077</u>	Not Issued	030	08/30/2001	METHODS FOR MAKING SEMICONDUCTOR STRUCTURES HAVING HIGH-SPEED AREAS AND HIGH-DENSITY AREAS	WANG, ZHONGZE
<u>10162289</u>	Not Issued	030	06/03/2002	TRANSISTOR FORMATION FOR SEMICONDUCTOR DEVICES	WANG, ZHONGZE
<u>10175774</u>	Not Issued	020	06/20/2002	METHODS OF FABRICATING A DIELECTRIC PLUG IN MOSFETS TO SUPPRESS SHORT-CHANNEL EFFECTS	WANG, ZHONGZE
<u>09741776</u>	Not Issued	071	12/19/2000	CHANNEL IMPLANT THROUGH GATE POLYSILICON	WANG, ZHONGZE
<u>09713844</u>	Not Issued	071	11/15/2000	METHOD OF FORMING A FIELD EFFECT TRANSISTOR	WANG, ZHONGZE
<u>10008854</u>	Not Issued	030	11/02/2001	TRANSISTOR STRUCTURE AND PROCESS TO FABRICATE SAME	WANG, ZHONGZE
<u>09810005</u>	Not Issued	071	03/16/2001	METHOD TO REDUCE TRANSISTOR CHANNEL LENGTH USING SDOX	WANG, ZHONGZE
<u>09808864</u>	Not Issued	030	03/15/2001	SUPPRESSION OF CROSS DIFFUSION AND GATE DEPLETION	WANG, ZHONGZE
<u>10002335</u>	Not	041	10/24/2001	METHODS OF FORMING	WANG,

	Issued			CONDUCTIVE CONTACTS	ZHONGZE
<u>10051981</u>	Not Issued	030	01/16/2002	SILICON-ON-INSULATOR COMPRISING INTEGRATED CIRCUITRY AND METHODS OF FORMING SILICON-ON-INSULATOR CIRCUITRY	WANG, ZHONGZE
<u>10087416</u>	Not Issued	041	02/27/2002	INTEGRATED CIRCUITRY AND SEMICONDUCTOR PROCESSING METHOD OF FORMING FIELD EFFECT TRANSISTORS	WANG, ZHONGZE
<u>10191833</u>	Not Issued	020	07/09/2002	METHOD OF USING HIGH-K DIELECTRIC MATERIALS TO REDUCE SOFT ERRORS IN SRAM MEMORY CELLS, AND A DEVICE COMPRISING SAME	WANG, ZHONGZE
<u>10205131</u>	Not Issued	020	07/24/2002	SIDEWALL STRAP FOR COMPLEMENTARY SEMICONDUCTOR STRUCTURES AND METHOD OF MAKING SAME	WANG, ZHONGZE

Inventor Search Completed: No Records to Display.

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